



SM Technology Co., Limited

SOT-23 Plastic-Encapsulate Transistors

MMBT4403 TRANSISTOR (PNP)

FEATURES

Switching transistor

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-35\text{V}$, $I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-35\text{V}$, $I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}$, $I_C=-150\text{mA}$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150\text{mA}$, $I_B=-15\text{mA}$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150\text{mA}$, $I_B=-15\text{mA}$		-0.95	V
Transition frequency	f_T	$V_{CE}=-10\text{V}$, $I_C=-20\text{mA}$ $f=100\text{MHz}$	200		MHz

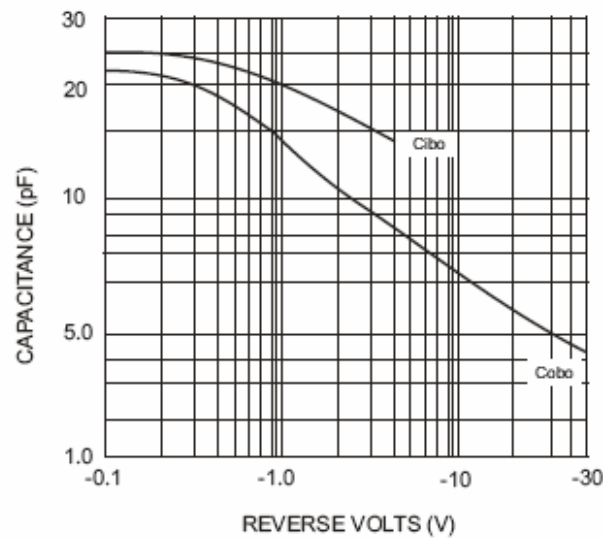


Fig. 1 Typical Capacitance

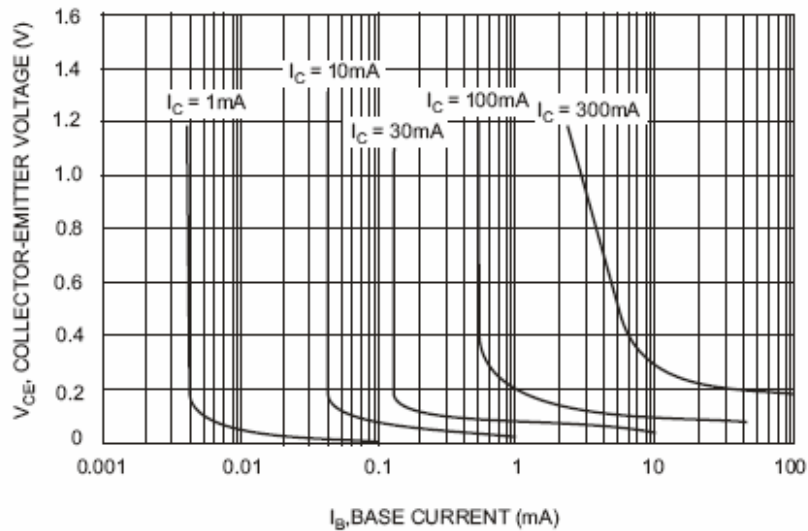


Fig. 2 Typical Collector Saturation Region

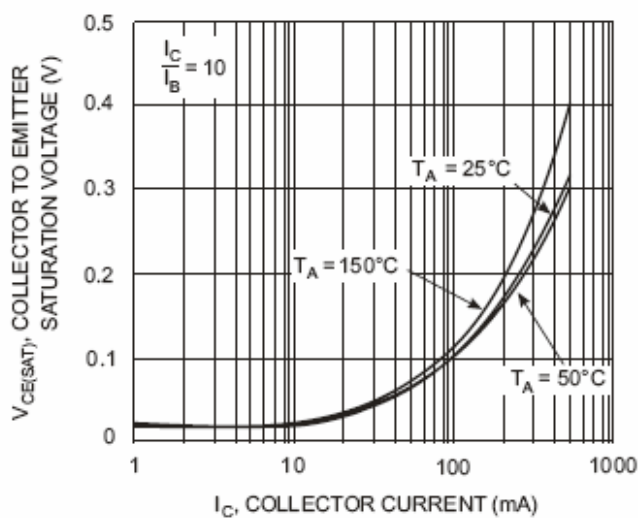


Fig. 3 Collector Emitter Saturation Voltage vs. Collector Current

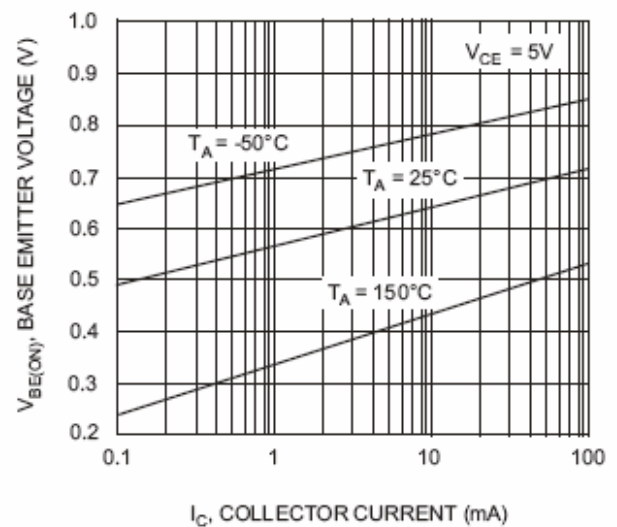


Fig. 4 Base-Emitter Voltage vs. Collector Current

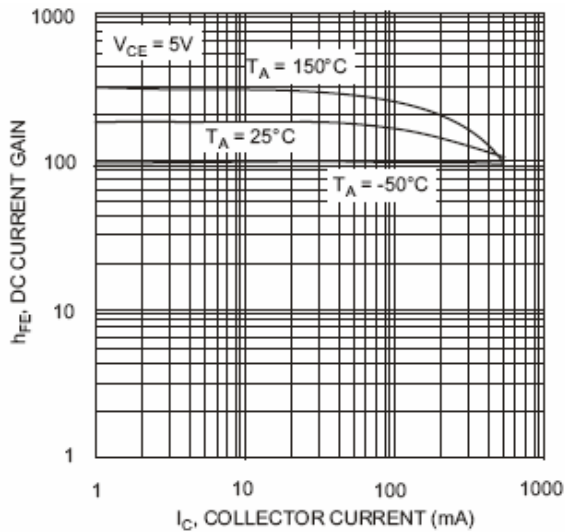


Fig. 5 DC Current Gain vs. Collector Current

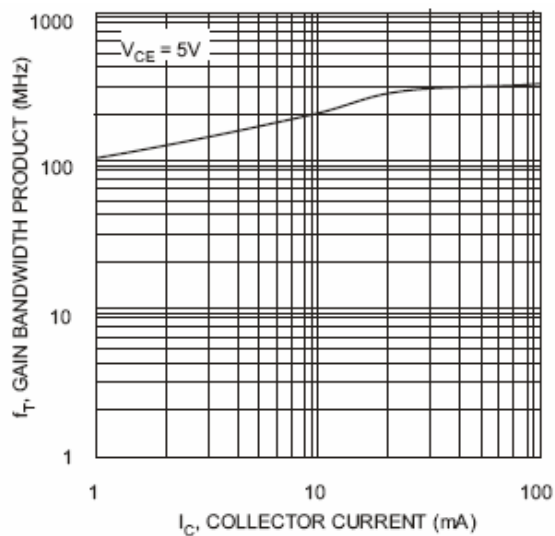


Fig. 6 Gain Bandwidth Product vs. Collector Current

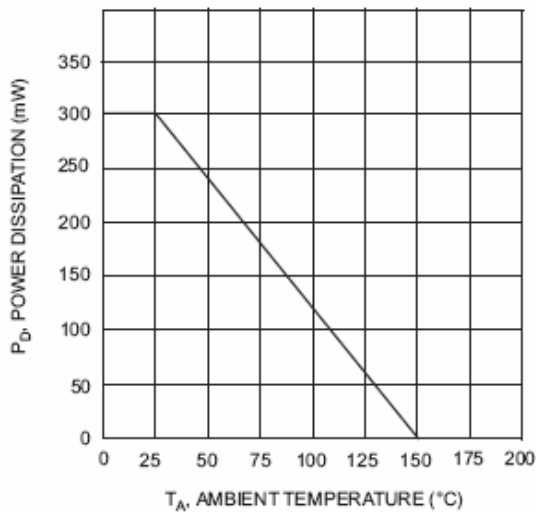


Fig. 7, Max Power Dissipation vs Ambient Temperature